RELIABILITY PREDICTION

- Assess whether reliability goals can be reached
- Identify potential design weaknesses
- Compare alternative designs
- Analyse life-cycle costs
- Plan logistic support strategies (ie, repairing ressources, ...)
- Establish objectives for reliability tests



Figure 1.1 - The Bathtub Curve

 λ : number of units failing per unit time



• Probability of failure, distribution function $F(t) = 1 - \exp(-\lambda t), \quad \lambda > 0$

Parameter λ (failure rate)

Reliability

$$R(t) = \exp(-\lambda t), \qquad \lambda > 0$$

Probability density function

$$f(t) = \frac{dF(t)}{dt} = \lambda \exp(-\lambda t)$$

Failure rate

$$\lambda(t) = \frac{f(t)}{1 - F(t)} = \lambda = const$$



Service Life / Life Time

25 years old humans have an MTBF of about 800 years



Reliability Prediction Assumes:

- The design is perfect, the stresses known, everything is within ratings at all times, so that only random failures occur
- Every failure of every part will cause the equipment to fail.
 - The component reliability database is valid



At Reference Conditions (Parts count)

$$\lambda_{S,i} = \sum_{i=1}^{n} \left(\lambda_{ref} \right)_{i},$$

where

 λ_{ref} is the failure rate under reference conditions; *n* is the number of components

Failure Rate Prediction

At Operating Conditions (Parts Stress)

$$\lambda = \sum_{i=1}^{n} \left(\lambda_{ref} \times \pi_U \times \pi_I \times \pi_T \right)_i$$

where

 $\begin{array}{lll} \lambda_{\mathrm{ref}} & \text{is the failure rate under reference conditions;} \\ \pi_{\mathrm{U}} & \text{is the voltage dependence factor;} \\ \pi_{\mathrm{I}} & \text{is the current dependence factor;} \\ \pi_{\mathrm{T}} & \text{is the temperature dependence factor;} \\ n & \text{is the number of components} \end{array}$

Prediction Methods



=>MTBF (250 kHours) @ Toperating (50°C)

Accelerated Life Testing

Acceleration Factor
$$AF = \frac{tf_1}{tf_2} = \exp\left(\frac{E}{k}\left(\frac{1}{T_1} - \frac{1}{T_2}\right)\right)$$

- tf_1 = time to failure at temperature T_1
- tf_2 = time to failure at temperature T_2
- T_1, T_2 = temperature in degrees Kelvin (°K)
- E = activation energy per molecule (eV)
- k = Boltzmann's constant (8.617 x 10^{-5} (eV/°K))

E from less than 0.3eV (gate oxide defect in a semiconductor) to more than 1.1eV (contact electro-migration)

MTBF vs Environmental Factors



MTBF vs Power Load & T°



Application

Buck Converter									
Composants	<u>λ</u> p	<u>πg</u>	πe	<u>πs</u>	πt	<u>πa</u>	πς	<u>λpart</u>	
Condensateur C1	0,05	0,7	6	1	1	1	1	0,21	
Condensateur C2	0,0044	0,7	6	1	1	1	1	0,01848	
				1	1	1	1		
Transistor TR1	0,012	0,7	6	1	2,5	4	1	0,504	
Diode D1	0,01	0,7	6	0,29	4,4	1	1	0,053592	
Self L1	0,026	0,7	6	1	1	1	1	0,1092	
Resistance de mesure	0,00044	0,7	6	1	1	1	6	0,011088	
Système								0,90636	
MTBF @ 50°C								1103314,3563	heures
								127	ans